SILICON A.M. BAND SWITCHING DIODE

The BA423 is a switching diode in **hermetically sealed glass DO-34 envelope.** Intended for band switching in a.m. radio receivers.

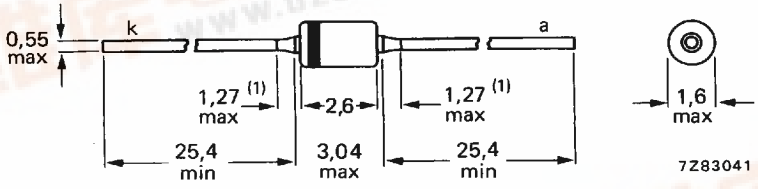
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	20	V
Forward current (d.c.)	I_F	max.	50	mA
Junction temperature	T_j	max.	150	°C
Diode capacitance at f = 1 MHz V_R = 3 V	C_d	<	2,5	pF
Series resistance at f = 1 MHz I_F = 10 mA	r_s	<	1,2	Ω

MECHANICAL DATA

Fig. 1 SOD-68 (DO-34).

Dimensions in mm



(1) Lead diameter in this zone uncontrolled.
The marking band indicates the cathode.
The diodes are type branded.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	20 V
Forward current (d.c.)	I_F	max.	50 mA
Storage temperature	T_{stg}	−65 to +	150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient in free air mounted on a printed-circuit board at a lead-length of 10 mm	$R_{th\ j\text{-}a}$	=	0,4 K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage I_F = 50 mA	V_F	<	0,9 V
Reverse current V_R = 20 V	I_R	<	100 nA
V_R = 20 V; T_j = 125 °C	I_R	<	5 μA
Diode capacitance at f = 1 MHz V_R = 3 V	C_d	<	2,5 pF
Series resistance I_F = 10 mA; f = 1 MHz	r_s	<	1,2 Ω

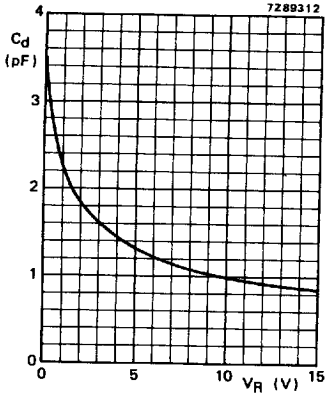


Fig. 2 Typical values
f = 1 MHz; T_j = 25 °C.

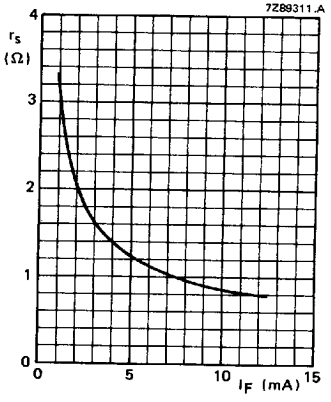


Fig. 3 Typical values
f = 1 MHz; T_j = 25 °C.